

Product data sheet

Product profile

1.1 General description

Logic level sensitive gate triac intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

Product availability:

MAC97A8 in SOT54 (TO-92) MAC97A6 in SOT54 (TO-92).

1.2 Features and benefits

- Blocking voltage to 600 V (MAC97A8)
 RMS on-state current to 0.6 A
- Sensitive gate in all four quadrants
- Low cost package.

1.3 Applications

- General purpose bidirectional switching
 Phase control applications
- Solid state relays.

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage				
	MAC97A8	T _j = 25 to 125 °C	_	600	V
	MAC97A6	T _j = 25 to 125 °C	_	400	V
I _{T(RMS)}	on-state current (RMS value)	full sine wave; T _{lead} ≤ 50 °C; Figure 5	_	0.6	Α
I _{TSM}	non-repetitive peak on-state current		_	8.0	Α



2. Pinning information

Table 2. Pinning - SOT54 (TO-92), simplified outline and symbol

Pin	Description	Simplified outline	Symbol	
1	main terminal 2	4	_	
2	gate	2,	1	
3	main terminal 1		2 msb033 3 mb/305	
		SOT54 (TO-92)		

3. Ordering information

Table 3. Ordering information

Type number	ype number Package		
	Name	Description	Version
MAC97A8	TO-92	Plastic single-ended leaded (through hole) package; 3 leads	SOT54
MAC97A6	TO-92	Plastic single-ended leaded (through hole) package; 3 leads	SOT54

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

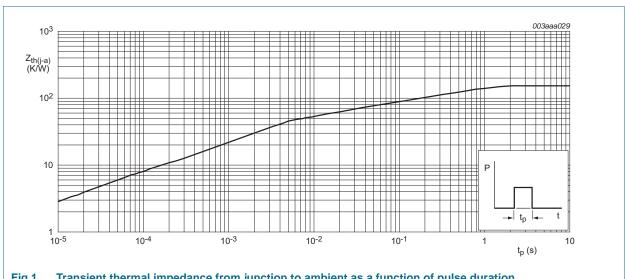
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage				
	MAC97A8	$T_j = 25 \text{ to } 125 ^{\circ}\text{C}$	_	600	V
	MAC97A6	$T_j = 25 \text{ to } 125 ^{\circ}\text{C}$	_	400	V
I _{T(RMS)}	on-state current (RMS value)	full sine wave; T _{lead} ≤ 50 °C; <u>Figure 5</u>	_	0.6	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; T _j = 25 °C prior to surge			
		t = 20 ms	_	8.0	Α
		t = 16.7 ms	_	8.8	Α
l ² t	I ² t for fusing	t = 10 ms	_	0.32	A ² s
dl _T /dt	repetitive rate of rise of on-state current after triggering	I_{TM} = 1.0 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μs			
		T2+ G+	_	50	A/μs
		T2+ G-	_	50	A/μs
		T2- G-	_	50	A/μs
		T2- G+	_	10	A/μs
I_{GM}	gate current (peak value)	t = 2 μs max	_	1	A
V_{GM}	gate voltage (peak value)	t = 2 μs max		5	V
P_{GM}	gate power (peak value)	t = 2 μs max	-	5	W
$P_{G(AV)}$	average gate power	T_{case} = 80 °C; t = 2 μ s max	_	0.1	W
T _{stg}	storage temperature		-40	+150	°C
Tj	operating junction temperature		-40	+125	°C

Thermal characteristics

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Value	Unit
$R_{th(j\text{-lead})}$	thermal resistance from junction to lead	full cycle	60	K/W
		half cycle	80	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on a printed circuit board; lead length = 4 mm; Figure 1	150	K/W

5.1 Transient thermal impedance



Transient thermal impedance from junction to ambient as a function of pulse duration.

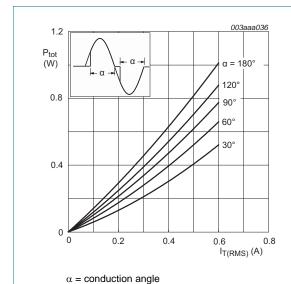
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6. Characteristics

Table 6. Characteristics

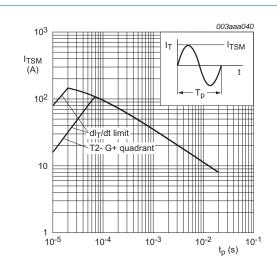
 $T_i = 25$ °C unless otherwise specified

aracteristics			Тур	Max	Unit
11 00101131103					
gate trigger current	V _D = 12 V; I _T = 0.1 A; <u>Figure 8</u>				
	T2+ G+	_	1	5	mA
	T2+ G-	-	2	5	mA
	T2- G-	-	2	5	mA
	T2- G+	-	4	7	mA
latching current	V _D = 12 V; I _{GT} = 0.1 A; <u>Figure 9</u>				
	T2+ G+	_	1	10	mA
	T2+ G-	-	5	10	mA
	T2- G-	-	1	10	mA
	T2- G+	_	2	10	mA
holding current	V _D = 12 V; I _{GT} = 0.1 A; <u>Figure 10</u>	-	1	10	mA
on-state voltage	I _T = 0.85 A; <u>Figure 11</u>	_	1.4	1.9	V
gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } \frac{\text{Figure 7}}{}$	_	0.9	2	V
	$V_D = V_{DRM}; I_T = 0.1 A; T_j = 110 ^{\circ}C$	0.1	0.7	-	V
off-state leakage current	$V_D = V_{DRM (max)}; T_j = 110 ^{\circ}C$	_	3	100	μΑ
characteristics					
critical rate of rise of off-state voltage	V_D = 67% of $V_{DM(max)}$; T_{case} = 110 °C; exponential waveform; gate open circuit; Figure 12	30	45	-	V/µs
critical rate of rise of commutation voltage	V_D = rated V_{DRM} ; T_{case} = 50 °C; I_{TM} = 0.84 A; commutating dl/dt = 0.3 A/ms	-	5	-	V/µs
gate controlled turn-on time	$I_{TM} = 1.0 \text{ A}; V_D = V_{DRM(max)};$ $I_G = 25 \text{ mA}; dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μS
	latching current holding current on-state voltage gate trigger voltage off-state leakage current characteristics critical rate of rise of off-state voltage critical rate of rise of commutation voltage gate controlled turn-on	$T2+ G+$ $T2+ G-$ $T2- G-$ $T2- G+$ $V_D = 12 \ V; \ I_{GT} = 0.1 \ A; \ \underline{Figure 9}$ $T2+ G+$ $T2+ G+$ $T2+ G-$ $T2- G-$ $T2- G-$ $T2- G+$ $holding current $	$T2+G+ \qquad \qquad -$ $T2+G- \qquad \qquad -$ $T2-G- \qquad \qquad -$ $T2-G+ \qquad \qquad -$ $Iatching current \qquad V_D = 12 \ V; \ I_{GT} = 0.1 \ A; \ Figure \ 9$ $T2+G- \qquad \qquad -$ $T2+G- \qquad \qquad -$ $T2-G- \qquad \qquad -$ $T2-G- \qquad \qquad -$ $T2-G+ \qquad \qquad -$ $T2-G+ \qquad \qquad -$ $holding current \qquad V_D = 12 \ V; \ I_{GT} = 0.1 \ A; \ Figure \ 10 \qquad -$ $on-state \ voltage \qquad I_T = 0.85 \ A; \ Figure \ 11 \qquad -$ $gate \ trigger \ voltage \qquad V_D = 12 \ V; \ I_T = 0.1 \ A; \ Figure \ 7 \qquad -$ $V_D = V_{DRM;} \ I_T = 0.1 \ A; \ Figure \ 7 \qquad -$ $V_D = V_{DRM} \ (max); \ T_j = 110 \ ^{\circ}C \qquad -$ $characteristics$ $critical \ rate \ of \ rise \ of \ off-state \ voltage \qquad V_D = 67\% \ of \ V_{DM(max)}; \ T_case = 110 \ ^{\circ}C; \ exponential \ waveform; \ gate \ open \ circuit; \ Figure \ 12}$ $critical \ rate \ of \ rise \ of \ commutation \ voltage \qquad V_D = rated \ V_{DRM;} \ T_{case} = 50 \ ^{\circ}C; \ -$ $I_{TM} = 0.84 \ A; \ commutating \ dI/dt = 0.3 \ A/ms$ $gate \ controlled \ turn-on \qquad I_{TM} = 1.0 \ A; \ V_D = V_{DRM(max)}; \qquad -$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$



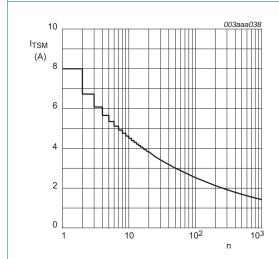
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Fig 2. Maximum on-state dissipation as a function of RMS on-state current; typical values.



 $t_{\text{p}} \leq 20 \text{ ms}$

Fig 3. Maximum permissible non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; typical values.



n = number of cycles at f = 50 Hz

Fig 4. Maximum permissible non-repetitive peak on-state current as a function of number of cycles for sinusoidal currents; typical values.

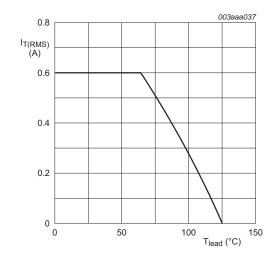


Fig 5. Maximum permissible RMS current as a function of lead temperature; typical values.

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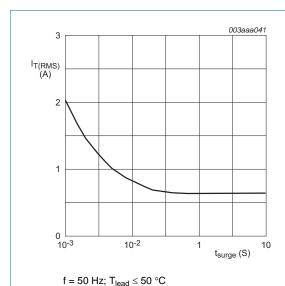
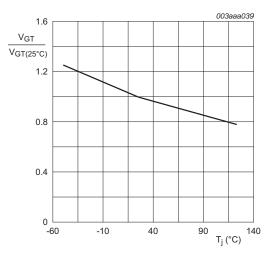


Fig 6. Maximum permissible repetitive RMS on-state current as a function of surge duration for sinusoidal currents; typical values.



$$a = \frac{V_{GT(Tj)}}{V_{GT(25^{\circ}C)}}$$

Fig 7. Normalized gate trigger voltage as a function of junction temperature; typical values.

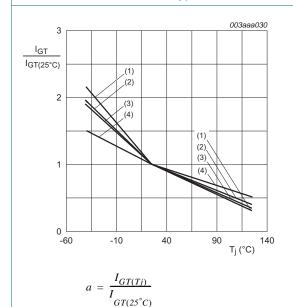
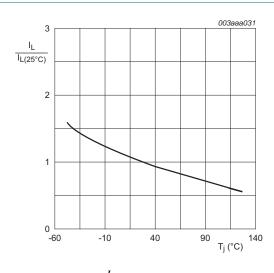


Fig 8. Normalized gate trigger current as a function of junction temperature; typical values.



 $a = \frac{I_{L(Tj)}}{I_{L(25^{\circ}C)}}$

Fig 9. Normalized latching current as a function of junction temperature; typical values.

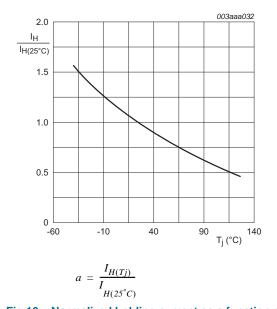


Fig 10. Normalized holding current as a function of junction temperature; typical values.

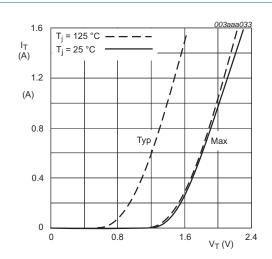


Fig 11. On-state current as a function of on-state voltage; typical and maximum values.

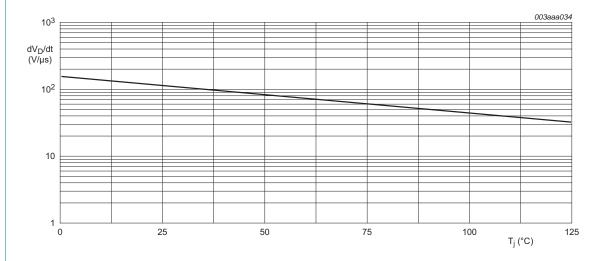


Fig 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values.

7. Package outline

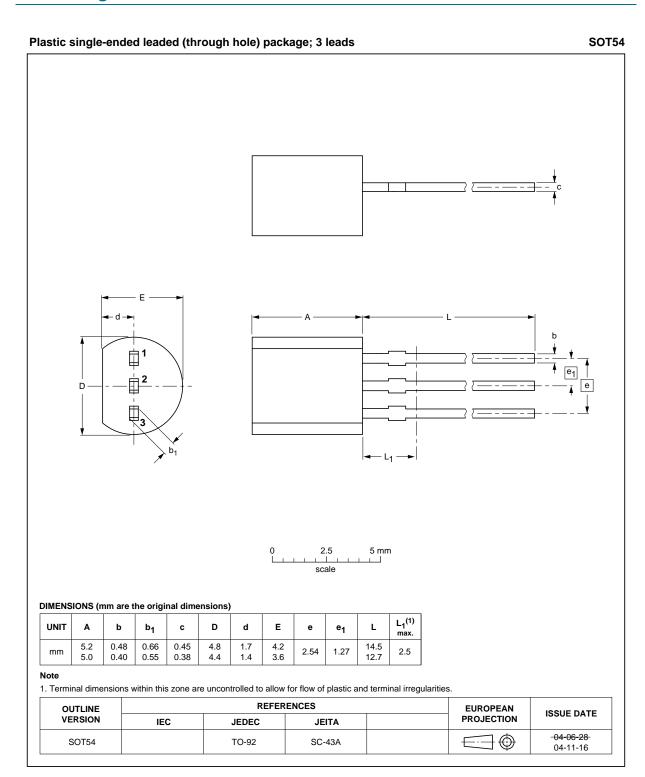


Fig 13. SOT54 (TO-92).

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
MAC97A8_A6 v.2	20110914	Product data sheet	-	MAC97A8_A6 v.1 (9397 750 07917)	
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 				
	 Legal texts 	have been adapted to the r	new company name whe	ere appropriate.	
	 Package or 	utline drawings have been u	pdated to the latest vers	sion.	
	Section 3 "	Ordering information" added	d.		
MAC97A8_A6 v.1 (9397 750 07917)	20010329	Product specification	-	-	

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions"
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Date of release: 14 September 2011 Document identifier: MAC97A8_A6